

	Type	Hits	Search Text	DBs	Time Stamp	Components	Error Definition	Errors
1	BRS	7	plasma with volt\$3 and implant\$5 with volt\$3 and potential and ion and chamber and cathode and anode and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 15:14			0
2	BRS	55	plasma with volt\$3 and implant\$5 with volt\$3 and potential and ion and chamber and cathode and anode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/06 10:39			0
3	BRS	1	increas\$3 with decreas\$3 with plasma with volt\$3 and increas\$3 with decreas\$3 with implant\$5 with volt\$3 and potential and ion and chamber and cathode and anode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/02 17:27			0
4	BRS	110	increas\$3 with decreas\$3 and plasma and implant\$5 and \$2generat\$3 and volt\$3 and potential and ion and chamber and cathode and anode and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 15:37			0

	Type	Hits	Search Text	DBs	Time Stamp	Components	Error Definition	Errors
5	BRS	22	puls\$3 with plasma with volt\$3 and puls\$3 with implant\$5 with volt\$3 and potential and ion and chamber and cathode and anode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 05 15:36			0
6	BRS	139	increas\$3 and decreas\$3 and plasma and implant\$5 and \$2generat\$3 and volt\$3 and potential and ion and chamber and cathode and anode and transistor and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 05 18:09			0
7	BRS	101	increas\$3 and decreas\$3 and plasma and implant\$5 and \$2generat\$3 and volt\$3 and potential and ion and chamber and cathode and anode and transistor and gate and nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 05 18:40			0
8	BRS	1	puls\$3 with plasma with volt\$3 and puls\$3 with implant\$5 with volt\$3 and potential and ion and chamber and cathode and anode and transistor and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 05 21:45			0

	Type	Hits	Search Text	DBs	Time Stamp	Components	Error Definition	Errors
9	BRS	6	plasma with volt\$3 and implant\$5 with volt\$3 and potential and ion and chamber and cathode and anode and transistor and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 05 21:50			0
10	BRS	49	increas\$3 and decreas\$3 and plasma and implant\$5 with gate and \$2generat\$3 and volt\$3 and potential and ion and chamber and cathode and anode and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 05 22:45			0
11	BRS	180	increas\$3 and decreas\$3 and plasma and implant\$5 and \$2generat\$3 and volt\$3 and potential and ion and chamber and cathode and anode and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 05 15:38			0
12	BRS	0	plasma with volt\$3 and implant\$5 with volt\$3 and potential and chamber and cathode and anode and nitrogen near gate near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 06 10:41			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	0	plasma with volt\$3 and implant\$5 with volt\$3 and potential and chamber and cathode and anode and nitrogen near gate near oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 06 10:42			0
14	BRS	0	plasma same volt\$3 and implant\$5 same volt\$3 and chamber and cathode and anode and nitrogen near gate near oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 06 10:44			0
15	BRS	7	plasma same volt\$3 and implant\$5 same volt\$3 and chamber and nitrogen near gate near oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 06 10:51			0
16	BRS	0	plasma same volt\$3 and implant\$5 same volt\$3 and chamber and nitrogen near gate near dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 06 10:50			0
17	BRS	10	plasma same volt\$3 and implant\$5 same volt\$3 and chamber and nitrogen near3 gate near3 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/ 06 11:00			0

	Type	Hits	Search Text	DBs	Time Stamp	Components	Error Definition	Errors
18	BRS	12	plasma same volt\$3 and implant\$5 same volt\$3 and chamber and ion near3 gate near3 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/06 11:01			0
19	BRS	9	plasma with generat\$3 and ion with implant\$3 with volt\$3 and potential and chamber and cathode and anode and transistor and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:03			0
20	BRS	4	plasma with generat\$3 with volt\$3 and ion with implant\$3 with volt\$3 and cathode and anode and transistor and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:06			0
21	BRS	5	plasma with generat\$3 with volt\$3 and ion with implant\$3 with volt\$3 and nitrogen and transistor and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:17			0
22	BRS	76	plasma same ion same nitrogen and implant\$3 and volt\$3 and transistor and gate and puls\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 16:50			0